

TOSHIBA VARIABLE CAPACITANCE DIODE SILICON EPITAXIAL PLANAR TYPE

1SV160

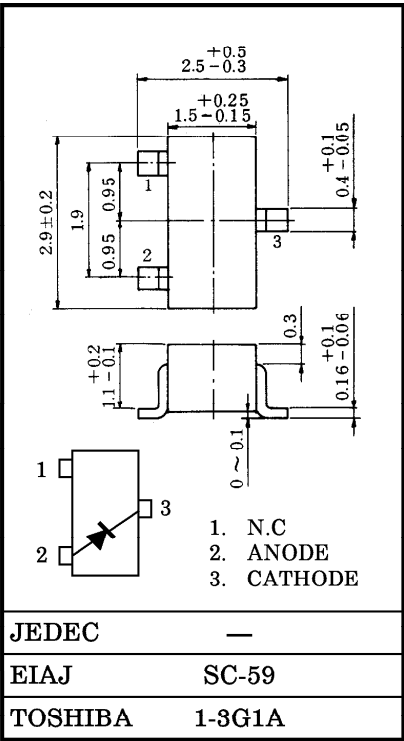
AFC APPLICATION FOR FM RECEIVER

Unit in mm

- Small Package.
- Low Series Resistance : $r_s = 0.7\Omega$ (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	15	V
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-55~125	°C

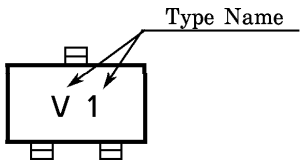


Weight : 0.012g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Current	I_R	$V_R = 4V$	—	—	100	nA
Reverse Voltage	V_R	$I_R = 10\mu A$	15	—	—	V
Total Capacitance	C_T	$V_R = 4V, f = 1MHz$	7	—	14	pF
Capacitance Ratio	C_{2V} / C_{4V}	—	1.2	—	1.5	—
Series Resistance	r_s	$V_R = 4V, f = 50MHz$	—	0.7	1.2	Ω

Marking



961001EAA2

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